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FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office					Docket No.		Serial No.		
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicants				
	(Us	e several sh	eets if nec	essary)	Wilbur G. Catabay et al.				
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	<u>L_</u>	QQ	5,939,763	8/17/99	Hao et al.	257	411	9/5/96	
		DE	5,864,172	1/26/99	Kapoor et al.	257	634	8/13/96	
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